of EEE201

# CMOS Digital Integrated Circuits

Department of Electrical & Electronic Engineering Xi'an Jiaotong-Liverpool University (XJTLU)

Tuesday, 7<sup>th</sup> November 2023

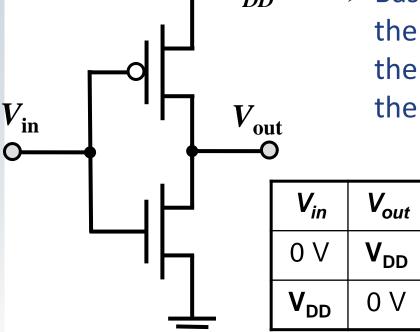
#### □ Building CMOS Logic Inverter

- Intuitive understanding from switch model
- transistor size determination
- > CMOS IC layout

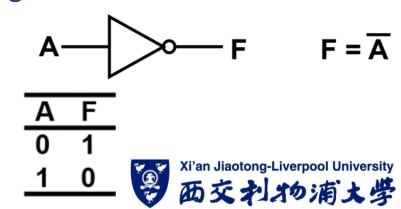


(one **p**MOS & one **n**MOS)

□ As the very first fundamental logic gate, a logic inverter (i.e. NOT logic gate) can be implemented using one pMOSFET stacking over one nMOSFET.

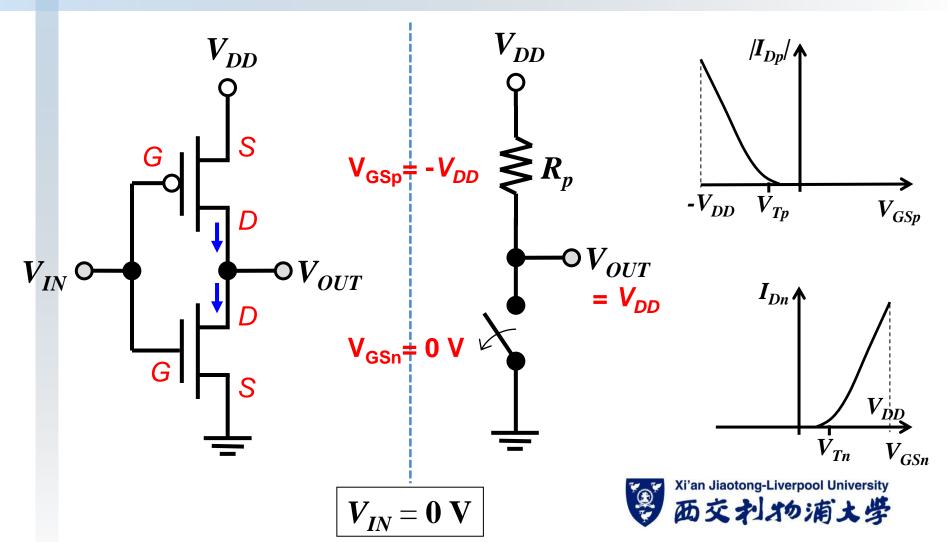


➤ Based on the device operation of the MOSFETs, we can easily find out the input-output relationship for the logic NOT function.



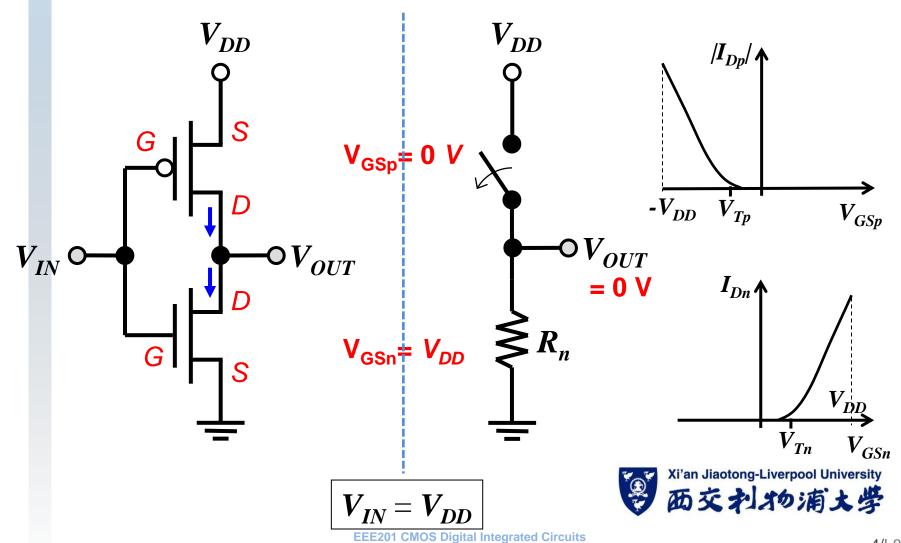
# CMOS Logic Inverter - $V_{in}$ = 0 V

(switch model for intuitive perspective)



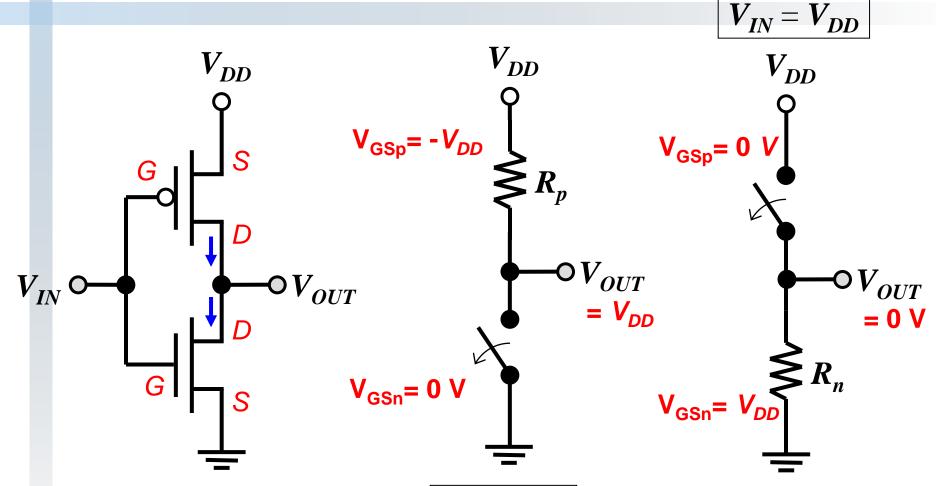
# CMOS Logic Inverter - $V_{in} = V_{DD}$

(switch model for intuitive perspective)



Semester 1, 2024/2025 by S.Lam@XJTLU

(only one switch is on in the steady state)



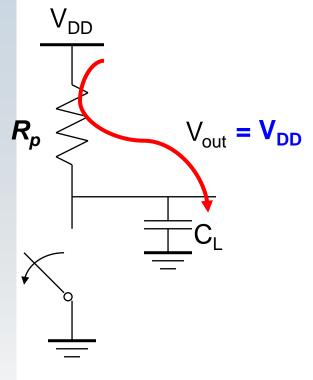
■ Note the "zero" <u>static</u> power consumption.

$$V_{IN} = 0 \text{ V}$$

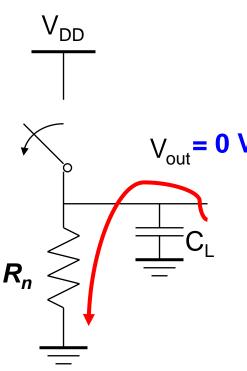


(dynamic behaviour in charging & discharging capacitances)

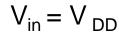
☐ Since there are **capacitances** associated with the MOSFETs, there will be **charging** and **discharging**.



$$V_{in} = 0$$

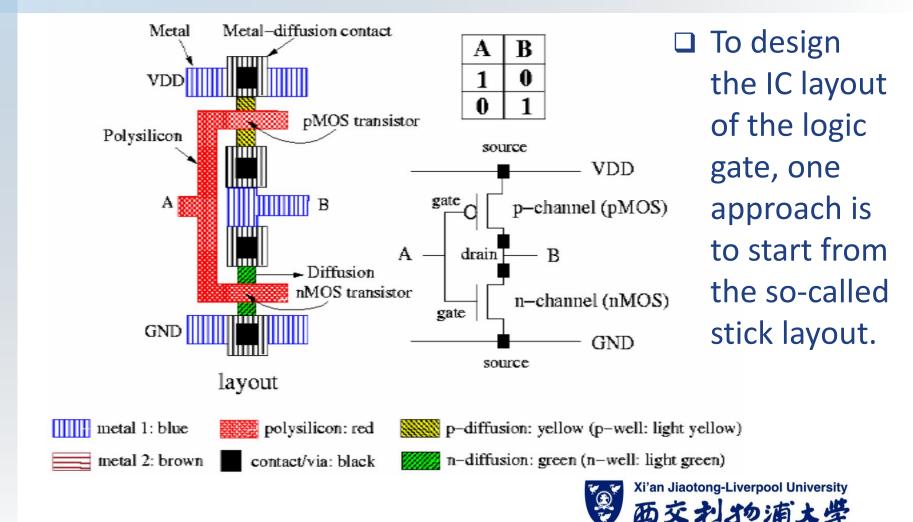


➤ The logic gate response time is determined by the time to charge C<sub>L</sub> through R<sub>p</sub> (discharge C<sub>L</sub> through R<sub>n</sub>).

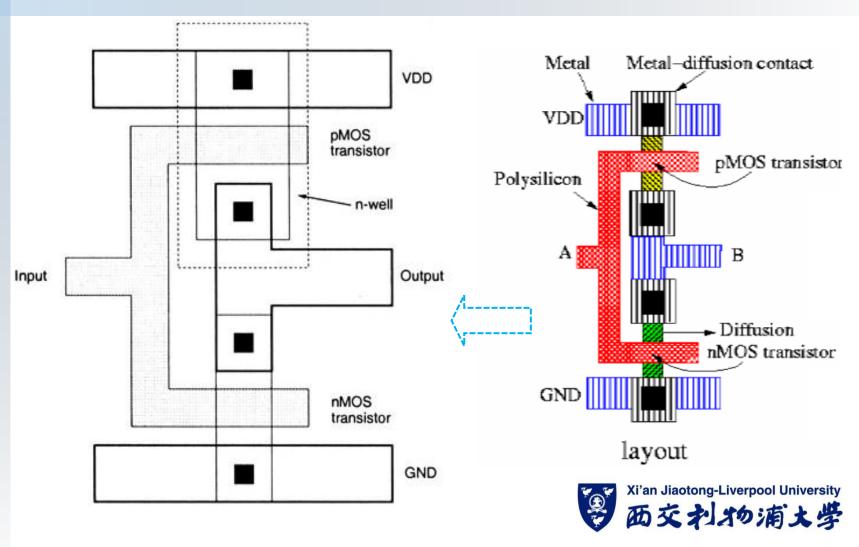




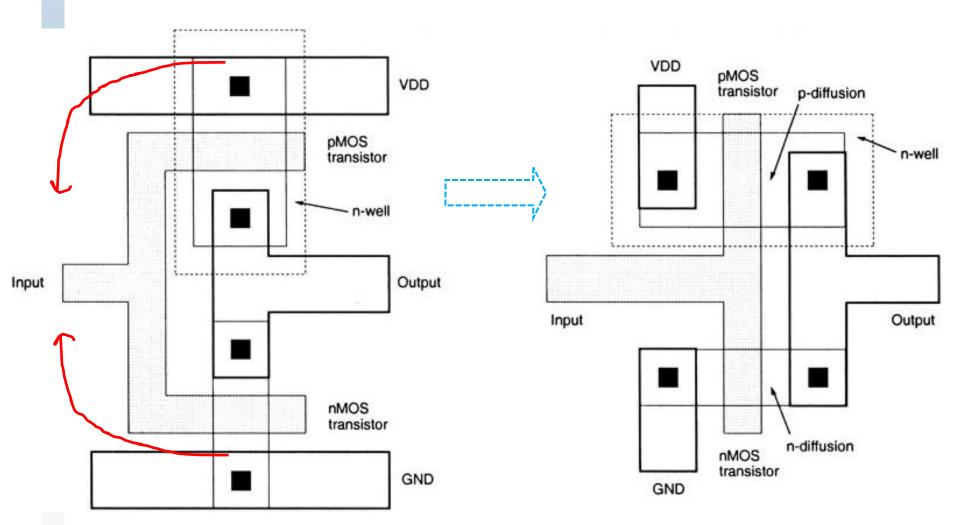
(start from stick layout diagram)



(scratch to proper layout)



(proper MOSFET layout orientation – less chip area)



(MOS transistor sizes – essential design consideration)

The sizes (W & L) of MOSFETs need to be designed in the layout.

$$| \text{If } V_{T0n} = |V_{T0p}|$$



$$I_{Dn} = I_{Dp}$$

$$or R_n = R_p$$

$$I_{D,sat} = \frac{1}{2} \mu_n C_{ox} \left( \frac{W}{L} \right) (V_{GS} - V_T)^2$$

$$I_{Dn} = I_{Dp} \qquad I_{D,sat} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right) (V_{GS} - V_T)^2$$

$$Or \ R_n = R_p \qquad I_{D,lin} = \mu_n C_{ox} \left(\frac{W}{L}\right) \left(V_{GS} - V_T\right) V_{DS} - \frac{V_{DS}^2}{2}$$



$$\mu_n \left(\frac{W}{L}\right)_n = \mu_p \left(\frac{W}{L}\right)_p$$

 $R_{n/p}$ : equivalent resistance of the MOSFET when turned on



GND

Input

VDD

pMOS

transistor

p-diffusion

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-diffusion

Output

(one **p**MOS & one **n**MOS)

- ☐ The **logic inverter** is an important start for understanding the operation and characteristics of CMOS logic circuits.
  - ➤ Digital circuits of a NAND and NOR logic gates can be reduced to a logic inverter. (Do you know why?)

